Ordering number:EN3770A

N-Channel Silicon MOSFET

2SK1469

Ultrahigh-Speed Switching Applications

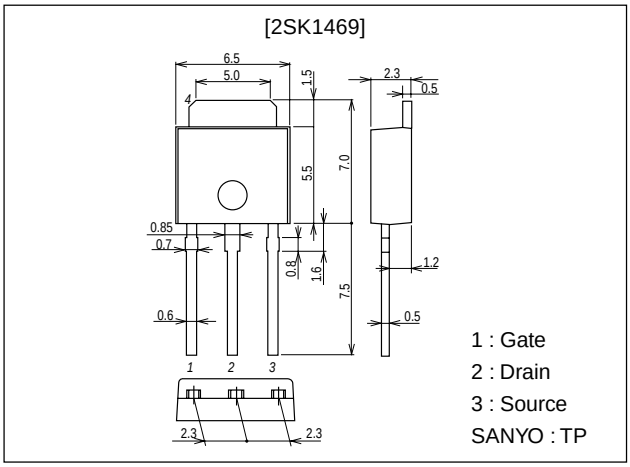
Features

- Low ON resistance.
- Ultrahigh-speed switching.
- Low-voltage drive.

Package Dimensions

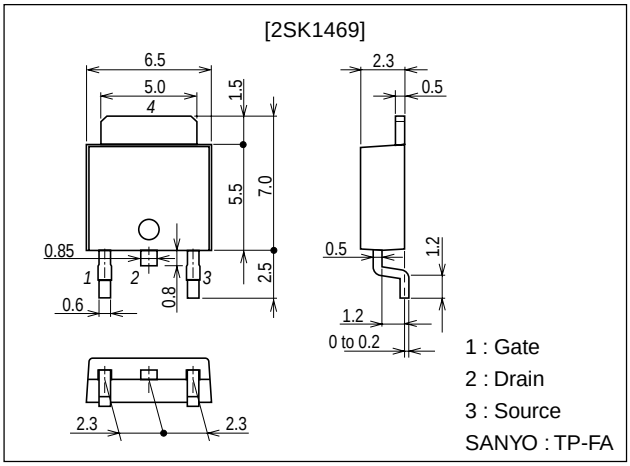
unit:mm

2083B



unit:mm

2092B



SANYO Electric Co.,Ltd. Semiconductor Company

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

Specifications

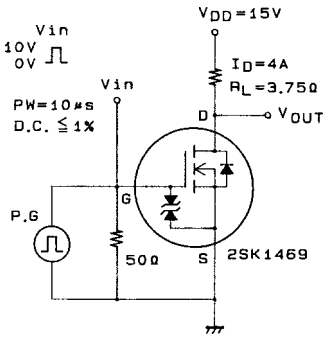
Absolute Maximum Ratings at Ta = 25˚C

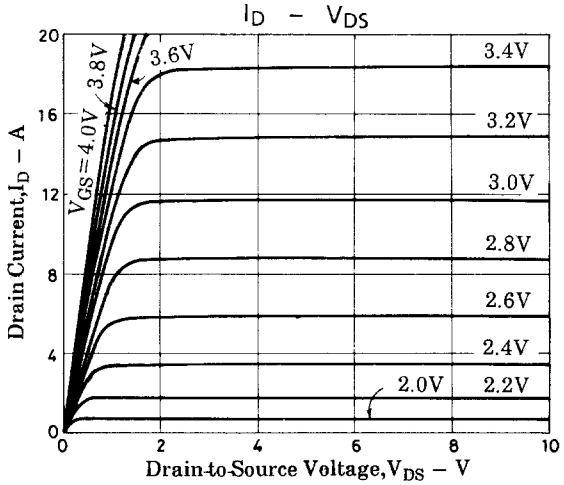
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		30	V
Gate-to-Source Voltage	V_{GSS}		±15	V
Drain Current (DC)	I_D		8	A
Drain Current (pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	32	A
Allowable Power Dissipation	P_D		1.0	W
		Tc=25°C	30	W
Channel Temperature	Tch		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

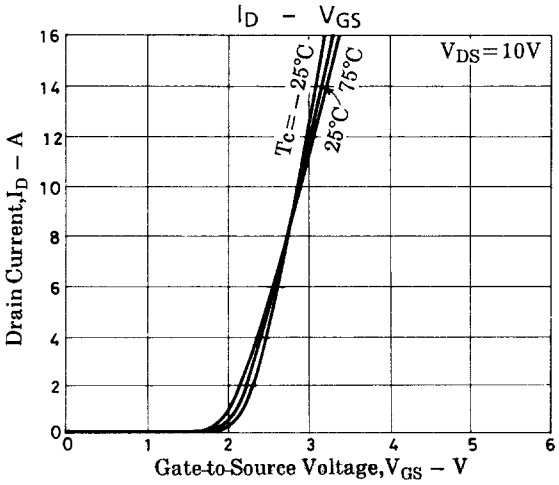
Electrical Characteristics at Ta = 25˚C

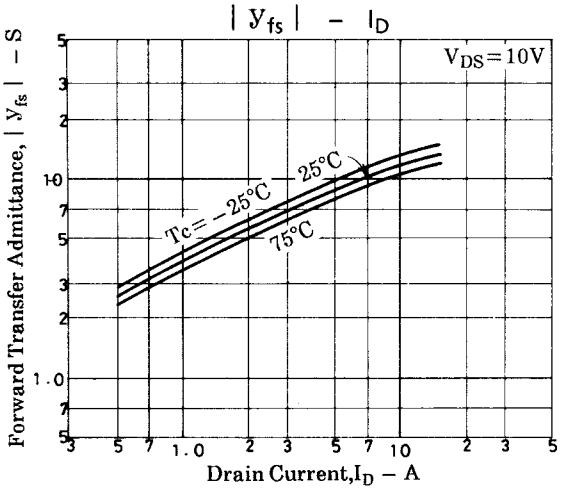
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	30			V
Gate-to-Source Breakdown Voltage	$V_{(BR)GSS}$	IG=±100μA, V_{DS}=0	±15			V
Zero-Gate Votlage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0			100	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±12V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=10V, I_D=1mA	1.0		2.0	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=4A	5	8		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}1$	I_D=4A, V_{GS}=10V		40	55	mΩ
	$R_{DS(on)}2$	I_D=4A, V_{GS}=4V		55	75	mΩ
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		1000		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		550		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		180		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		13		ns
Rise Time	t_r	See specified Test Circuit		40		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		130		ns
Fall Time	t_f	See specified Test Circuit		120		ns
Diode Forward Voltage	V_{SD}	I_S=8A, V_{GS}=0		1.0	1.5	V

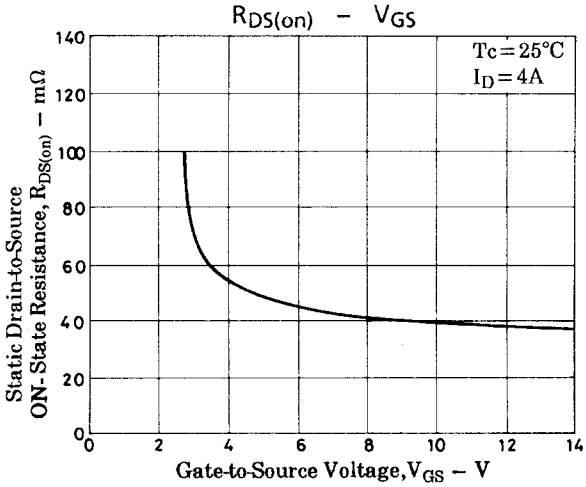
Switching Time Test Circuit

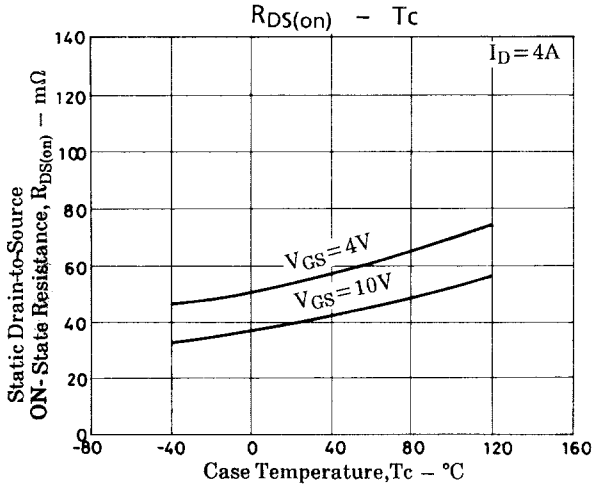


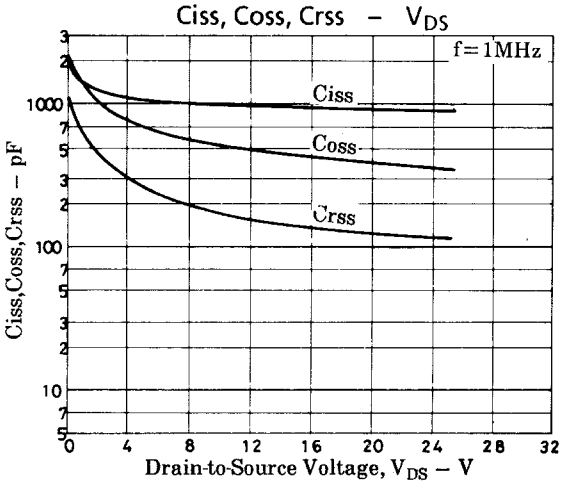

ID – VDS
Drain Current,ID – A
Drain-to-Source Voltage,VDS – V
VGS=4.0V
3.8V
3.6V
3.4V
3.2V
3.0V
2.8V
2.6V
2.4V
2.2V
2.0V

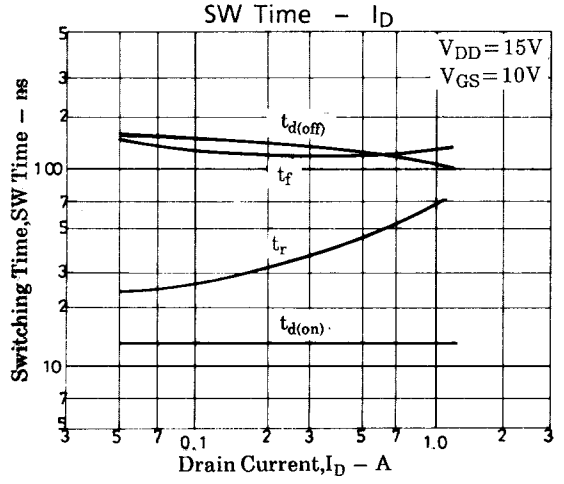

ID – VGS
Drain Current,ID – A
Gate-to-Source Voltage,VGS – V
VDS=10V
Tc=–25°C
25°C
75°C

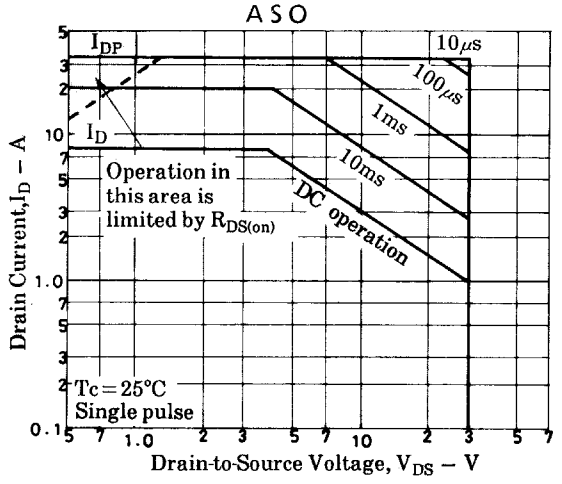

| yfs | – ID
Forward Transfer Admittance, | yfs | – S
Drain Current,ID – A
VDS=10V
Tc=–25°C
25°C
75°C


RDS(on) – VGS
Static Drain-to-Source ON-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage,VGS – V
Tc=25°C
ID=4A


RDS(on) – Tc
Static Drain-to-Source ON-State Resistance, RDS(on) – mΩ
Case Temperature,Tc – °C
ID=4A
VGS=4V
VGS=10V


Ciss, Coss, Crss – VDS
Ciss,Coss,Crss – pF
Drain-to-Source Voltage, VDS – V
f=1MHz
Ciss
Coss
Crss


SW Time – ID
Switching Time,SW Time – ns
Drain Current,ID – A
VDD=15V
VGS=10V
td(off)
tf
tr
td(on)


A S O
Drain Current,ID – A
Drain-to-Source Voltage, VDS – V
IDP
ID
10μs
100μs
1ms
10ms
DC operation
Operation in this area is limited by RDS(on)
Tc=25°C
Single pulse